

■ Productor Character

- Half Bridge Rectified、Common Cathode Structure.
- Multilayer Metal -Silicon Potential Structure.
- Beautiful High Temperature Character.
- Have Over Voltage protect loop, high reliability.
- RoHs Product.

■ Primary Use

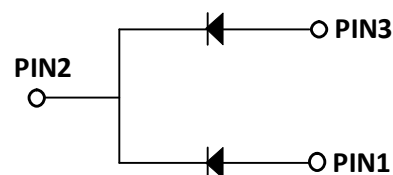
- Low Voltage High Frequency Switching Power Supply.
- Low Voltage High Frequency Invers Circuit.
- Low Voltage Continued Circuit and Protection Circuit.

■ Summarize

- MBR1060CT/MBR1060FCT Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications.

Device Weight :

ITO-220AB-1.48g TO-220AB-1.96g TO-263-1.78g



Absolute Maximum Ratings

| Item | Symbol | Data | Unit |
|---|------------------|-----------|------|
| Maximal Inverted Repetitive Peak Voltage | VRRM | 60 | V |
| *Average Rectified Forward Current (Rated VR-20Khz Square Wave) - 50% duty cycle | IFAV | 10 | A |
| Typical Thermal Resistance (per leg Package =TO-220AB/TO-263 Package =ITO-220AB) | R _{θJc} | 2 | °C/W |
| | | 4 | °C/W |
| Forward Peak Surge Current(Rated Load 8.3 Half Mssine Wave-According to JEDEC Method) | IFSM | 120 | A |
| Maximum Rate of Voltage Change (at Rated VR) | dv/dt | 10000 | V/uS |
| Peak Repetitive Reverse Surge Current (2uS-1Khz) | IRRM | 1 | A |
| Operating Junction Temperature | TJ | -40- +150 | °C |
| Storage Temperature | TSTG | -40- +150 | °C |

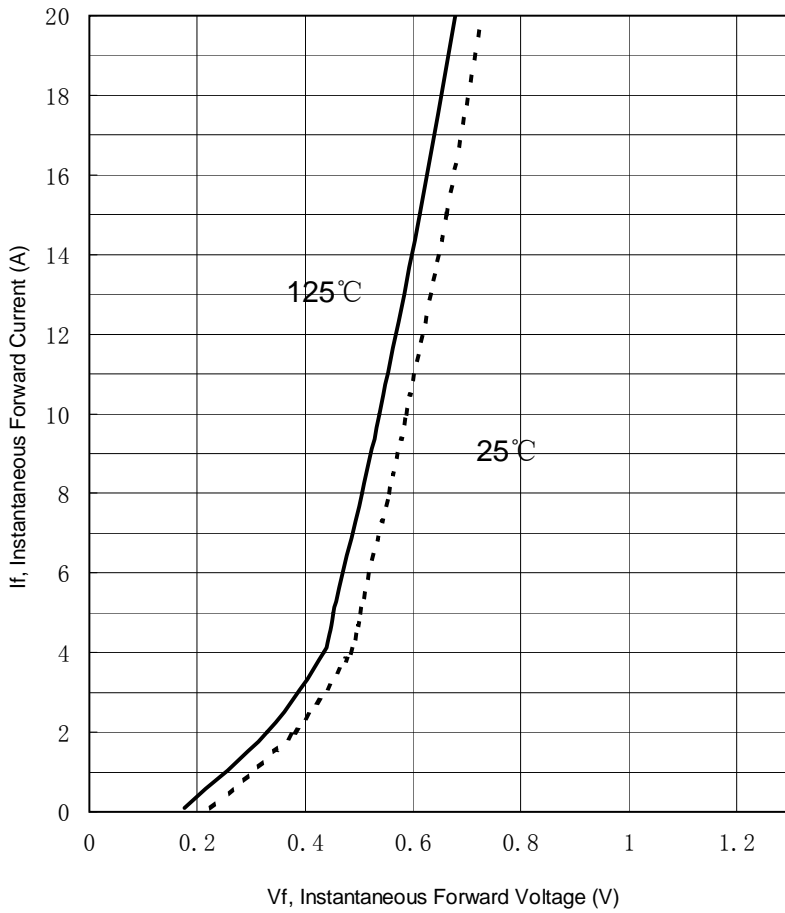
Electricity Character

| Item | Test Condition | | TYP. | MAX. | Unit |
|------|----------------|---------|------|------|------|
| IR | TJ =25°C | VR=VRRM | | 20 | uA |
| | TJ =125°C | | | 2 | mA |
| VF | TJ =25°C | IF=5A | 0.62 | 0.64 | V |
| | TJ =125°C | IF=5A | | 0.56 | V |

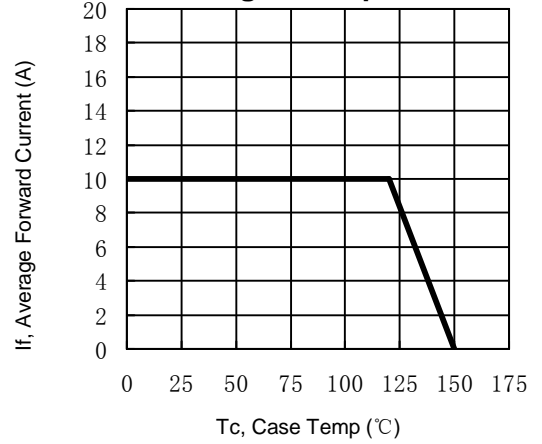
*IF(AV)= 5A×2

Characteristic Curves

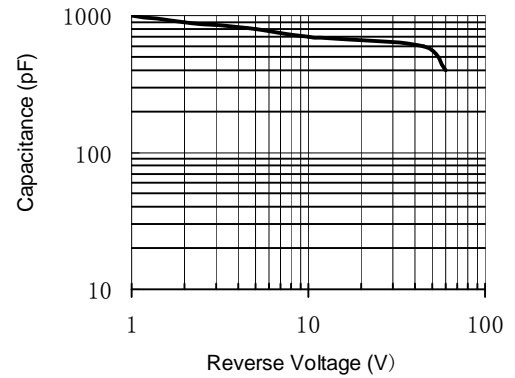
The forward voltage and forward current curve



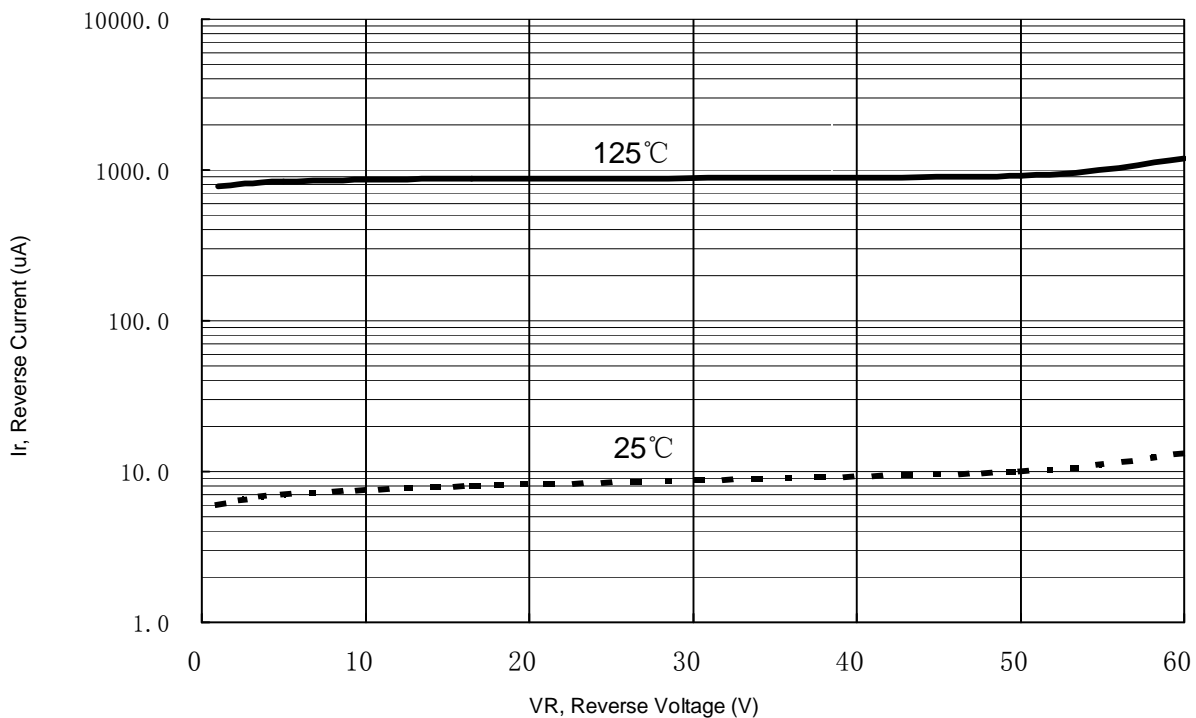
Current derating curve, per element



The crunode capacitance curve

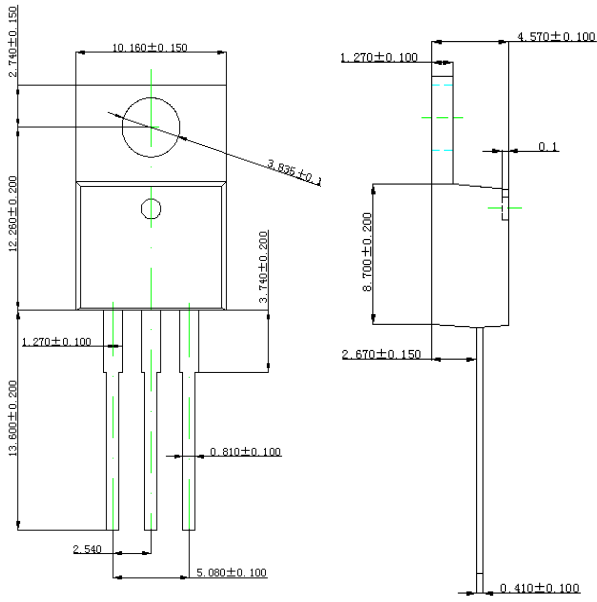


The reverse leak current and the reverse voltage (single-device) curve.

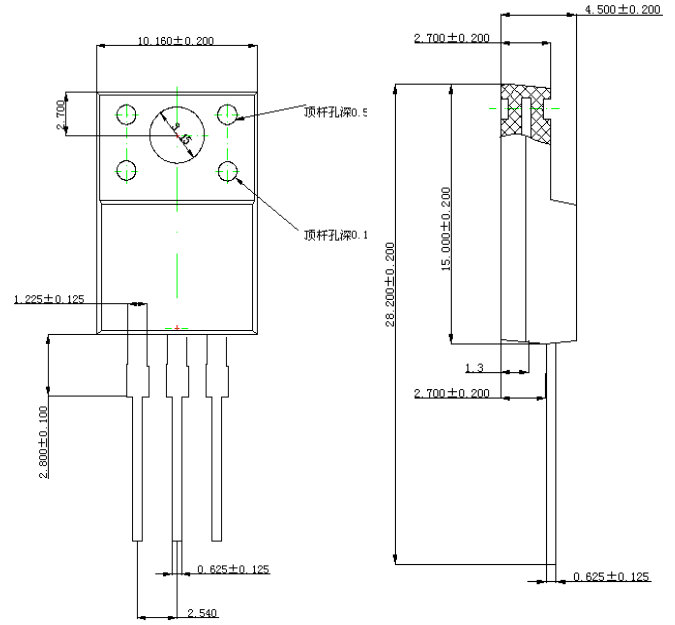


Package Outline Dimensions

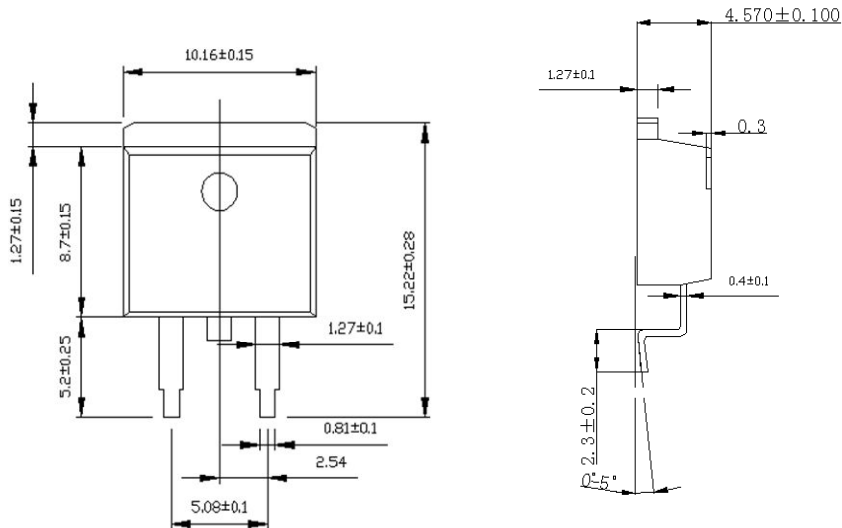
TO-220



ITO-220

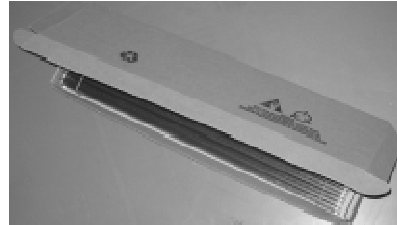
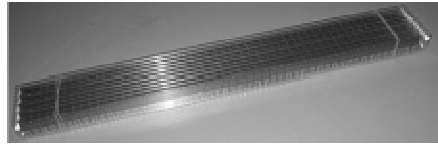


TO-263



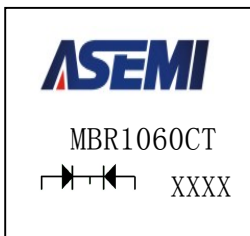
Packing Information

| Part Number | Package | Delivery Mode |
|-------------|---------------|------------------|
| MBR1060CT | TO-220/TO-263 | 50 pieces / tube |
| MBR1060FCT | ITO-220 | 50 pieces / tube |



| Part Number | Quantity | Size (mm) |
|-----------------|-------------|-------------|
| tube | 50 pieces | 530*33*7 |
| inner box | 1000 pieces | 560*150*40 |
| outer container | 5000 pieces | 580*230*170 |

Marking



- 1.ASEMI为LOGO。
- 2.MBR1060CT为产品型号。
- 3.XXXX代表日期码，第一码表示公元年的最后一码，第二码表示生产时当月码（A,B,C...为一月，二月，三月...），第三，四码表示大量生产时批次码例如:2013年第一月生产的，D/C为3AXX。
- 4.ITO-220封装后面加“F”区别



High-Voltage Schottky Diodes

MBR1060CT/MBR1060FCT

Label

内盒标签（尺寸：125*32mm）格式：

PART NO.: XXXXXX



DATE: 20140526 DE27



Q'TY: 1000 PCS



RoHS



PART NO: 产品型号;

DATE CODE:产品周号;

QTY:实物数量;

例如: XXXXXXXX/3J43/1000/20130615001016

外箱标签（尺寸：75*64mm）格式：



RoHS

PART NO.: XXXXXX



DATE: 20140526 DE27



Q'TY: 5000 PCS



PART NO:产品型号;

DATE:产品包装日期;

QTY:产品数量

注意事项

- 1) 凡本公司出厂的产品，均符合相应规格书的电参数和外形尺寸要求；对于客户有特殊要求的产品,双方应签订相关技术协议。
- 2) 在安装时，要注意减少机械应力的产生，安装扭矩推荐值0.3牛/米，防止由此引起的产品失效。
- 3) 避免靠近发热元件；焊接上锡时要注意控制温度和时间，焊接温度小于260℃，10S。
- 4) 产品储存需注温度与湿度的控制，一般情况下，温度在5℃-25℃，湿度50%条件下，可存放一年，过保存期后，使用前需重新测试。
- 5) 静电及高压会对产品产生损坏，使用和检验产品时，佩戴防静电腕带或手套，设备工具可靠接地。